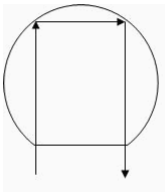
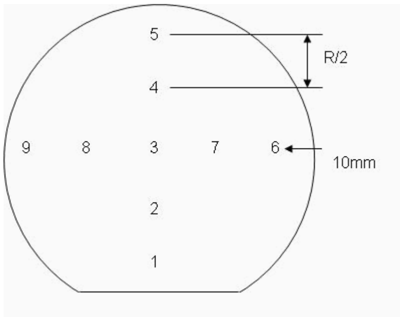
Icemos Technology Ltd **Product Specification** **1003.290401** Issue Date 10 July 2014 14:52:27

Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	WaferVendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	Any	Wafer Vendor
	6.0	Dopant	Any	Wafer Vendor
	7.0	Resistivity	0.1~ 100 ohm cm	Wafer Vendor
	8.0	Overall Thickness	650.00 +/- 25.00 um	Wafer Vendor
	9.0	Total Thickness Variation (TTV)	<3.00um	Guaranteed by process
	10.0	Bow	<50.00um	ADE to ASTM F534, 20%
	11.0	Warp	<50.00um	ADE to ASTM F657, 20%
	12.0	Lasermarking	On wafer FRONTSIDE opposite the flat as per attachment. Scribe format: [ICE-6-650.XXXX] (unique scribe)	Guaranteed by process
	13.0	Orientation	<100> +/-0.5	Wafer Vendor
	14.0	Back Surface Quality	Polished with light handling marks.	Guaranteed by process
	15.0	Front Surface Quality	Prime polished	Guaranteed by process
	16.0	Edge Chips	None	Bright Light 100% (note 2)
HandleSilicon	17.0	Handle Thickness	650.00 +/- 25.00 um	ADE
	18.0	Surface Haze	None	Bright Light, 100% (note 2).
	19.0	Total scratch length	None	Bright Light, 100% (note 2).

Part Number Customer

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	
Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below: 		
Additional Information			